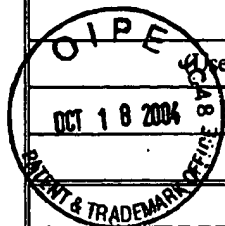


U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SNDK.257US2	10/799,180
(Use several sheets if necessary)	Applicant(s)	Conf. No.
	Jack H. Yuan et al.	8152
	Filing Date	Group
	March 12, 2002	2812 2825



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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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